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FORM PT01449 U.S. DEPARTMENT OF SOMMERCE ATTY, DOCKET NO. SERIAL NO. PATENT AND TRADEMARK OFFICE (REV. 8-83) 09/114504 HARI.006USQ APPLICANT INFORMATION DISCLOSURE STATEMENT ELIYAHOU HARARI et al. (Use several sheets if necessary) GROUP FILED 2824 HEREWITH **U. S. PATENT DOCUMENTS** •EXAMINER SUB FILING DOCUMENT NUMBER DATE NAME **CLASS** INITIAL **CLASS** DATE ۳.8 Al 7/75 Cricchi et al. 6 A2 3 8 9 8 6 3 2 8/75 Spencer, Jr. **A3** 3 9 0 6 5 9/75 4 5 Houston et al. A4 9 4 7 5 0 Hadden, Jr. 10/75 **A5** 4 0 4 9 4 3 3 8/77 Berg **A6** 4 0 5 8 7 9 9 11/77 George et al. **A7** 4 0 6 4 4 0 5 12/77 Cricchi et al. **A8** 5 5 1 8 9/78 Houston et al. Α9 4 3 0 8 9 Adam 0 12/78 A10 4 1 4 1 0 8 l 2/79 Home et al. 34 9 3/80 Brewer FOREIGN PATENT DOCUMENTS SUB TRANS.? DOCUMENT NUMBER DATE COUNTRY **CLASS CLASS** (YES/NO BI JP 58 0 1983 Japan **Abstract** B2 JP 58 5 7 9 1983 2 1 4 Japan **Abstract B3** JP 58 2 5 7 9 5 1983 1 Japan Yes B4 JP 59 6 1984 2 6 9 5 19 Japan **Abstract B5** JP 62 3 7 4 9 12/1987 Japan **Abstract** OTHER DOCUMENTS (Including Author, Title, Date, Pertinent pages, Etc.) C1 Flash Memory Cards, Oct. 1992, pp. 4-91, 4-95, and 4-96. Cricchi et al., "Nonvolitile Block-Oriented RAM", IEEE International Solid-State Circuits Conference, Feb, سو 13-15, 1974, Digest of Technical Papers. Brewer et al., "Block-Oriented Random Acess MNOS Memory", National Computer Conference and Jul. Exposition, Chicago, May 6-10, 1974, AFIPS Conference Proceedings, vol 43. Pp. 837-840. DATE CONSIDERED EIVED EXAMINER Vu JAN U-4-1999

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